

**IN THE CLAIMS:**

Amend the following claims:

1. (Currently Amended) A polishing apparatus which imparts relative motion between a layer with a concave portion and a convex portion on a semiconductor wafer, comprising: and a polishing tool having a plane polishing surface to polish the surface of said semiconductor wafer by said plane polishing surface of said polishing tool, comprising:

a polishing tool comprising a grindstone and having a plane polishing surface to polish the surface of said semiconductor wafer by said plane polishing surface of said grindstone;

a dressing tool having a plane dressing surface for forming a surface roughness on the plane polishing surface of said polishing tool grindstone;

a first moving means for imparting relative motion in a direction horizontal to the plane polishing surface of said polishing tool grindstone between said dressing tool and said polishing tool;

a second moving means for moving said dressing tool in a direction vertical to the plane polishing surface of said polishing tool grindstone; and

a control means for permitting to execute movement caused by said first moving means while controlling a position of said second moving means.

2. (Currently Amended) The polishing apparatus according to claim 1, wherein said polishing tool grindstone is formed of abrasive grain and a material for joining and holding said abrasive grain.

3. (Original) The polishing apparatus according to claim 1, wherein said dressing tool includes a plurality of kinds of hard grain.

4. (Original) The polishing apparatus according to claim 3, wherein said hard grain is diamond.

5. (Currently Amended) The polishing apparatus according to claim 1, wherein said control means comprises a detection means for detecting contact of said polishing tool

grindstone with said dressing tool and controls to stop said second moving means on the basis of the detection of contact between said ~~polishing tool~~ grindstone and said dressing tool by said detection means.

6. (Currently Amended) The polishing apparatus according to claim 1, wherein said first moving means moves said dressing tool, said ~~polishing tool~~ grindstone or both of them so that said dressing tool moves on said polishing tool.

7. (Currently Amended) The polishing apparatus according to claim 1, wherein said control means comprises a setting means for setting a cut-in amount of said dressing tool with respect to said ~~polishing tool~~ grindstone, and said second moving means moves in accordance with a value set by said setting means.

8. (Original) The polishing apparatus according to claim 7, wherein said control means realizes the cut-in amount set by said setting means by moving said second moving means plural times.

9. (Currently Amended) The polishing apparatus according to claim 8, wherein the cut-in amount by said setting means is set to be smaller than depth required to stick the hard grain contained in said dressing tool into said ~~polishing tool~~ grindstone.

10. (Currently Amended) A polishing apparatus which imparts relative motion between a layer with a concave portion and a convex portion, comprising: and a polishing tool having a plane polishing surface to polish the surface of said semiconductor wafer by said plane polishing surface of said polishing tool, comprising:

a polishing tool comprising a grindstone and having a plane polishing surface to polish the surface of said semiconductor wafer by said plane polishing surface of said grindstone;

a dressing tool having a plane dressing surface for forming a surface roughness on the plane polishing surface of said ~~polishing tool~~ grindstone; and

a means for inhibiting movement of said dressing tool in a direction vertical to the polishing surface of said ~~polishing tool~~ grindstone.

11. (Currently Amended) A method for manufacturing a semiconductor for effecting polishing-processing while pressing a thin film surface adhered to a surface of a semiconductor substrate formed with an irregularity pattern to the polishing surface of a ~~polishing tool~~ grindstone for relative motion comprising:

forming a surface roughness with a dressing tool on the polishing surface of said ~~polishing tool~~ grindstone, during a period between polishing processing or during the polishing process, while controlling ~~movement~~ a position of said dressing tool in a vertical direction with respect to said polishing surface.